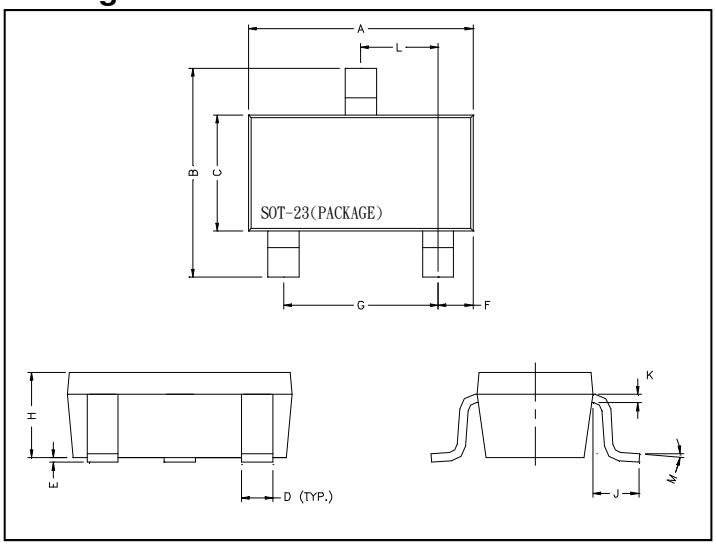
GMBT9014

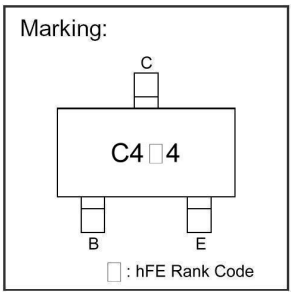
NPN EPITAXIAL TRANSISTOR

Description

The GMBT9014 is designed for general purpose amplifier applications.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	VCBO	50	V
Collector to Emitter Voltage	VCEO	45	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	IC	100	mA
Total Power Dissipation	PD	225	mW

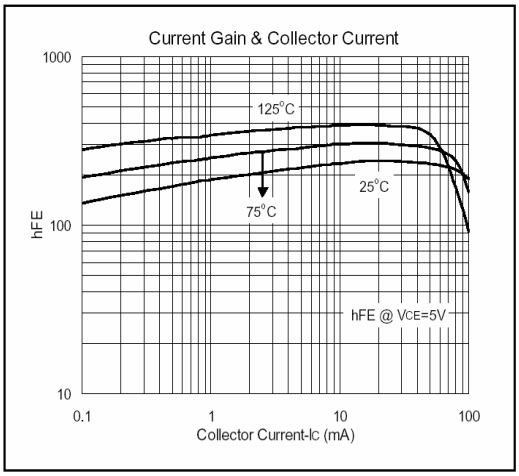
Characteristics at Ta = 25℃

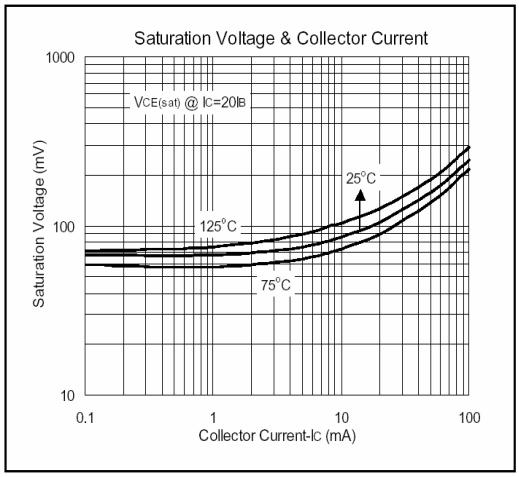
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	50	-	-	V	IC=100uA , IE=0
BVCEO	45	-	-	V	IC=1mA, IB=0
BVEBO	5	-	-	V	IE=100uA, IC=0
ICBO	-	-	50	nA	VCB=50V, IE=0
IEBO	-	-	50	nA	VEB=5V, IC=0
VCE(sat)	-	0.14	0.3	V	IC=100mA, IB=5mA
VBE(sat)	-	0.84	1	V	IC=100mA, IB=5mA
VBE(on)	0.58	0.63	0.7	V	VCE=5V, IC=2mA
hFE	100	280	1000		VCE=5V, IC=1mA
fT	150	270	-	MHz	VCE=5V, IC=10mA
Cob	-	2.20	3.5	pF	VCB=10V, f=1MHz, IE=0

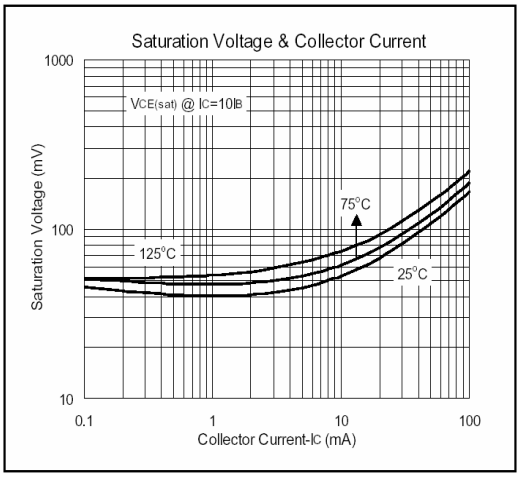
Classification Of hFE

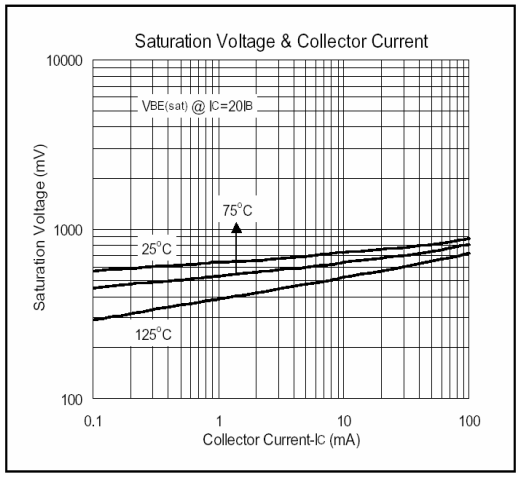
Rank	B	C	D
hFE	100 - 300	200-600	400-1000

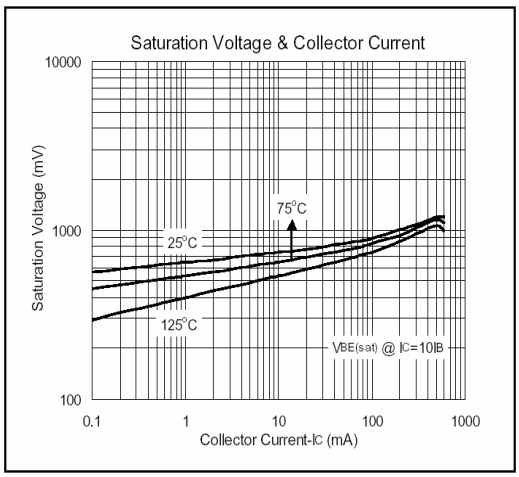
Characteristics Curve

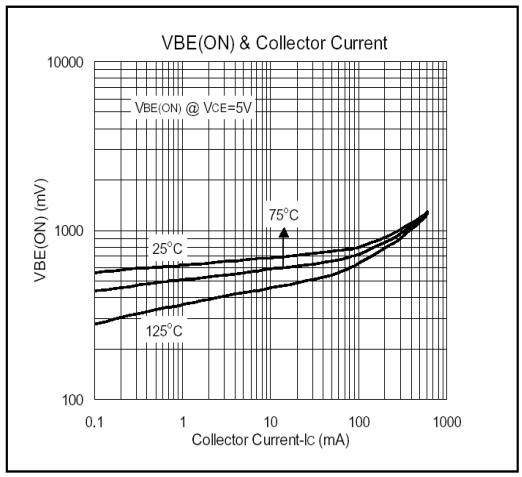


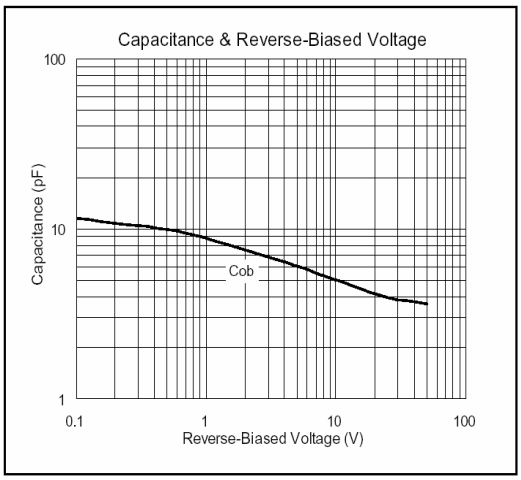


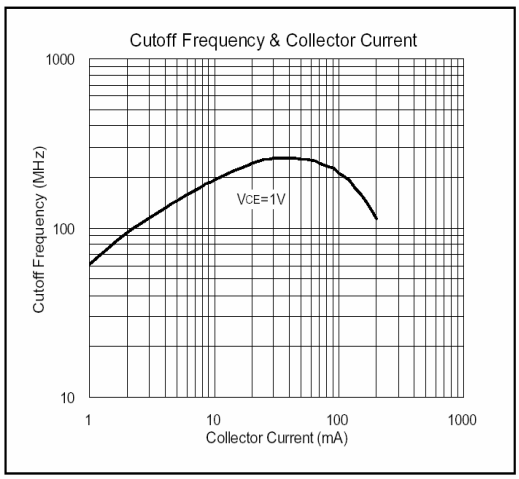












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